

Features

- High Power Handling
- Low Loss / Low Distortion
- Passivated Chip for Low Leakage Current
- Low Theta (θ)
- Fully RoHS* Compliant

Applications

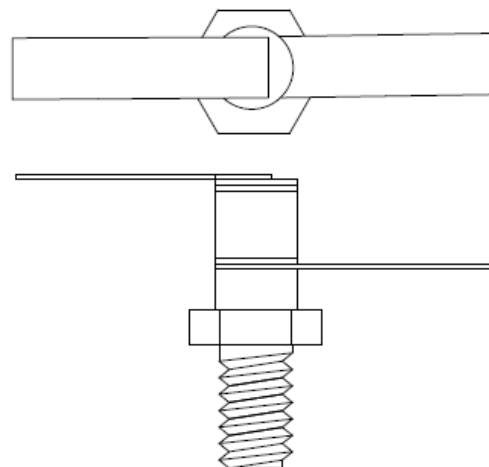
- MRI

Description

The HIPAX series of PIN diodes are designed for usage in switch and attenuator applications requiring high power handling and low distortion. These diodes incorporate a fully passivated PIN diode chip resulting in an extremely low reverse bias leakage current. The semiconductor technology utilized in the HIPAX families draws on MACOM's substantial experience in PIN diode design and wafer fabrication. The result is a device which has a thick I-region and long carrier lifetime while maintaining low series resistance and capacitance values. The chips used in the HIPAX PIN diodes are enclosed in a rugged ceramic package and is full face bonded to metal pins on both the anode and cathode. The result is a low loss PIN diode with low thermal resistance due to symmetrical thermal paths.

The MADP-07001B-1458WN is a BeO isolated packaged PIN diode well suited for MRI applications requiring a series diode but needing excellent power handling and heat management. The package leads are gold plated and compatible with both leaded and lead free solder attach processes. The base stud is OFHC copper which gives good heat management due to its high thermal conductivity.

ODS-1458



HIPAX PIN diodes are designed for use in a wide variety of switch and attenuator applications from HF through UHF frequencies and at power levels above 1 kW, CW. The internal chip as well as each diode assembly has been comprehensively tested and characterized to ensure predictable and repeatable performance.

Many of MACOM's HIPAX PIN diodes are also available as chips. Please consult the "Silicon PIN Chip Datasheet" for availability and specifications.

Ordering Information

Package Style	Devices Per Container
ODS-1458	25

* Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

Electrical Specifications @ $T_A = +25^\circ\text{C}$

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Reverse Voltage Rating	100 V	μA	—	—	1
Series Resistance	100 mA, 100 MHz	Ω	—	—	0.75
Total Capacitance	100 V, 1 MHz	pF	—	—	.8
Parallel Resistance	100 V, 100 MHz	k Ω	—	75	—
Carrier Lifetime	$I_F = 10 \text{ mA}$, $I_R = 6 \text{ mA}$	μs	—	8	—
Forward Voltage	100 mA	V	—	—	1.0
Reverse Current	At max. rated voltage	μA	—	—	1
Nominal I-Region Width	—	μm	—	175	—

Condition	P_{DISS}	θ_{JC}
Heat Sink Connection	30 W	5°C/W
Single 1 μs pulse	15 kW	—
Single 100 μs pulse	300 W	0.5°C/W

Absolute Maximum Ratings
 $T_A = +25^\circ\text{C}$ (Unless Otherwise Noted)^{1,2}

Parameter	Absolute Maximum
DC Reverse Voltage	500 V
Operating Chip Junction Temperature	-55°C to $+175^\circ\text{C}$
Storage Temperature	-55°C to $+175^\circ\text{C}$
Installation Temperature	$+280^\circ\text{C}$ for 30 Seconds

- Exceeding any one or combination of these limits may cause permanent damage to this device.
- MACOM does not recommend sustained operation near these survivability limits.

Handling Procedures

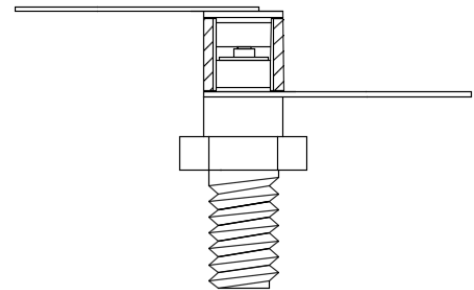
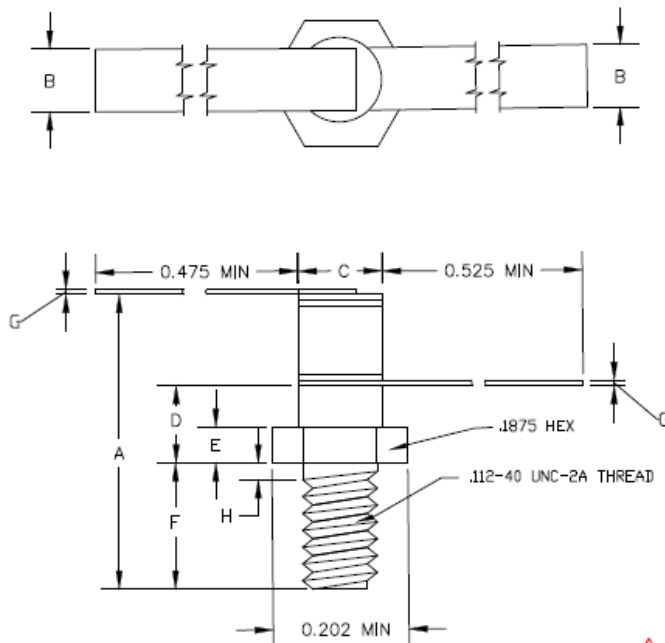
Please observe the following precautions to avoid damage:

Static Sensitivity

These electronic devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these HBM Class 1A devices.

Isolated Stud Package

Internal Construction



DIM	INCHES		MM	
	MIN.	MAX.	MIN.	MAX.
A	.414	.462	10,52	11,74
B	.090	.105	2,29	2,67
C	.119	.135	3,02	3,43
D	.107	.127	2,72	3,23
E	.050	.060	1,27	1,52
F	.183	.193	4,65	4,90
G	.002	.010	0,05	0,25
H	—	.030	—	0,76

ODS-1458 Assembly Recommendations

Bends on the ODS-1458 axially leaded devices must be made while holding the lead firm and forming the bend no closer than 0.060 inches from the body of the part. Bending the lead <0.060 inches from the body of the part is not recommended and may cause internal damage to the chip. Appropriate fixturing should be used.

Devices may be soldered using standard 60Sn/40Pb or any RoHS compliant solders. Axial leads are tin plated 50 µm thick to ensure an optimum connection. For recommended Sn/Pb and RoHS soldering profiles see Application Note M538 on the MACOM website.

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